

## Certificate of Analysis (CoA)

Dec. 8, 2025

**Product Name:** Germanium Telluride Sputtering Target (GeTe<sub>4</sub>)

**Chemical Formula:** GeTe<sub>4</sub>

**Purity:** 99.999% (5N)

**Dimensions:** Ø76.2 mm × 3.0 mm (±0.1 mm)

**Backing Plate:** None

**Quantity:** 1 pc

**Lot Number:** CSJM-251207TB

**Manufactured by:** Thin-Film Materials

### Physical Description

- Form: Semiconductor/compound sputtering target
- Appearance: Dark gray to black, dense ceramic-like surface
- Fabrication: High-purity vacuum melting and precision machining
- Typical Phase: Hexagonal Ge–Te compound (Te-rich)

### Chemical Composition (by ICP-OES / GDMS)

Element	Symbol	Max. Content (ppm)
Germanium	Ge	Balance
Tellurium	Te	Balance
Oxygen	O	<20
Carbon	C	<20
Silicon	Si	<10
Aluminum	Al	<10
Iron	Fe	<10
Calcium	Ca	<10
Magnesium	Mg	<10
Copper	Cu	<10
Other elements (each) –	–	<5
<b>Total Impurities</b>	–	<50 ppm

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### Handling & Storage

- Store in vacuum-sealed packaging.
- Avoid moisture and rapid temperature changes.
- Handle with clean gloves to prevent contamination.

### Declaration

This product has been manufactured and tested according to our quality control standards and meets the specifications stated herein.

### Authorized Signature:

Inspection Certificate by: Nancy Liu

Approver by: Chen Qiang

